

PHOTOLUMINESCENCE DYNAMICS OF GaAs/AlGaAs CORE-SHELL NANOWIRES

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Materials for 1-D Devices

- Why look at semiconductor nanowires?

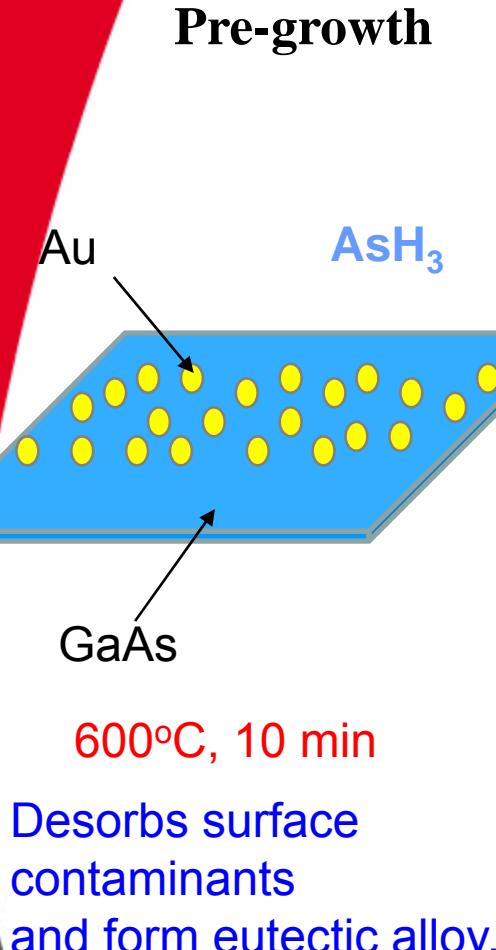
Applications

- Sensor development
- LED and Nanowire lasers
- Photo detectors
- Single electron devices

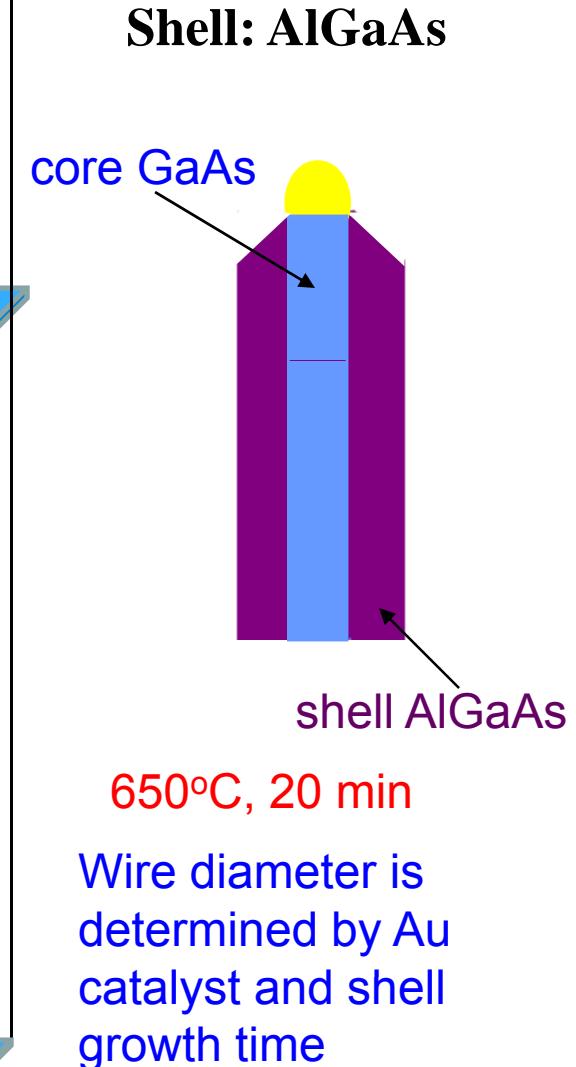
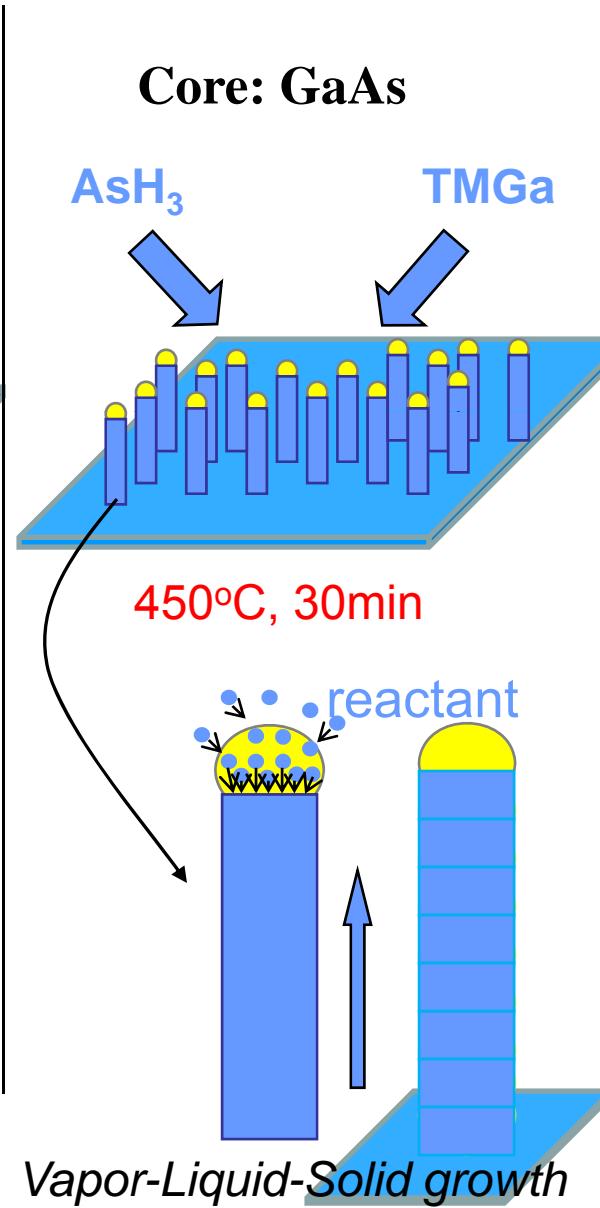


*All depend on
material quality*

Core-Shell Nanowire Growth

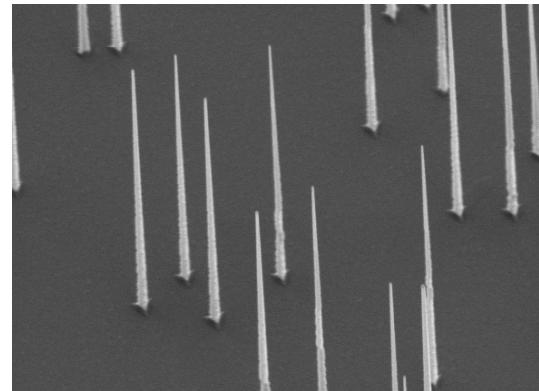


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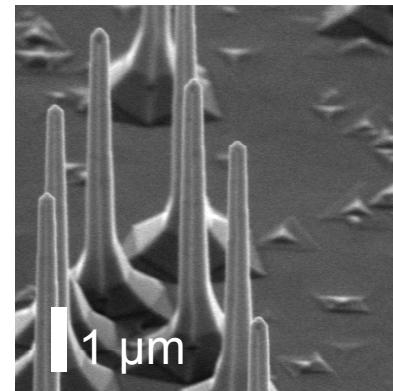


SEM of GaAs/AlGaAs grown at 450 C

GaAs
core

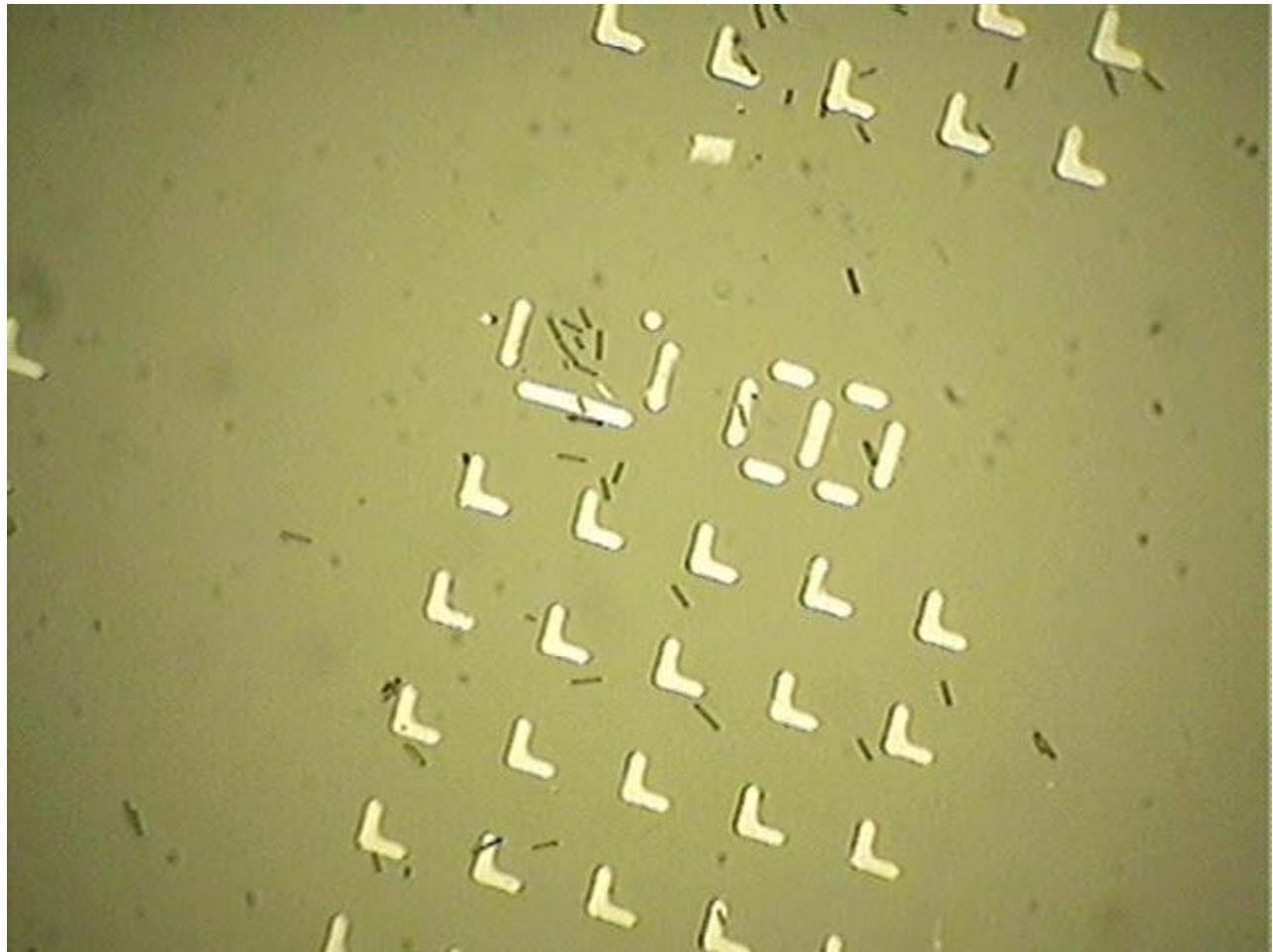


GaAs/AlGaAs
core-shell

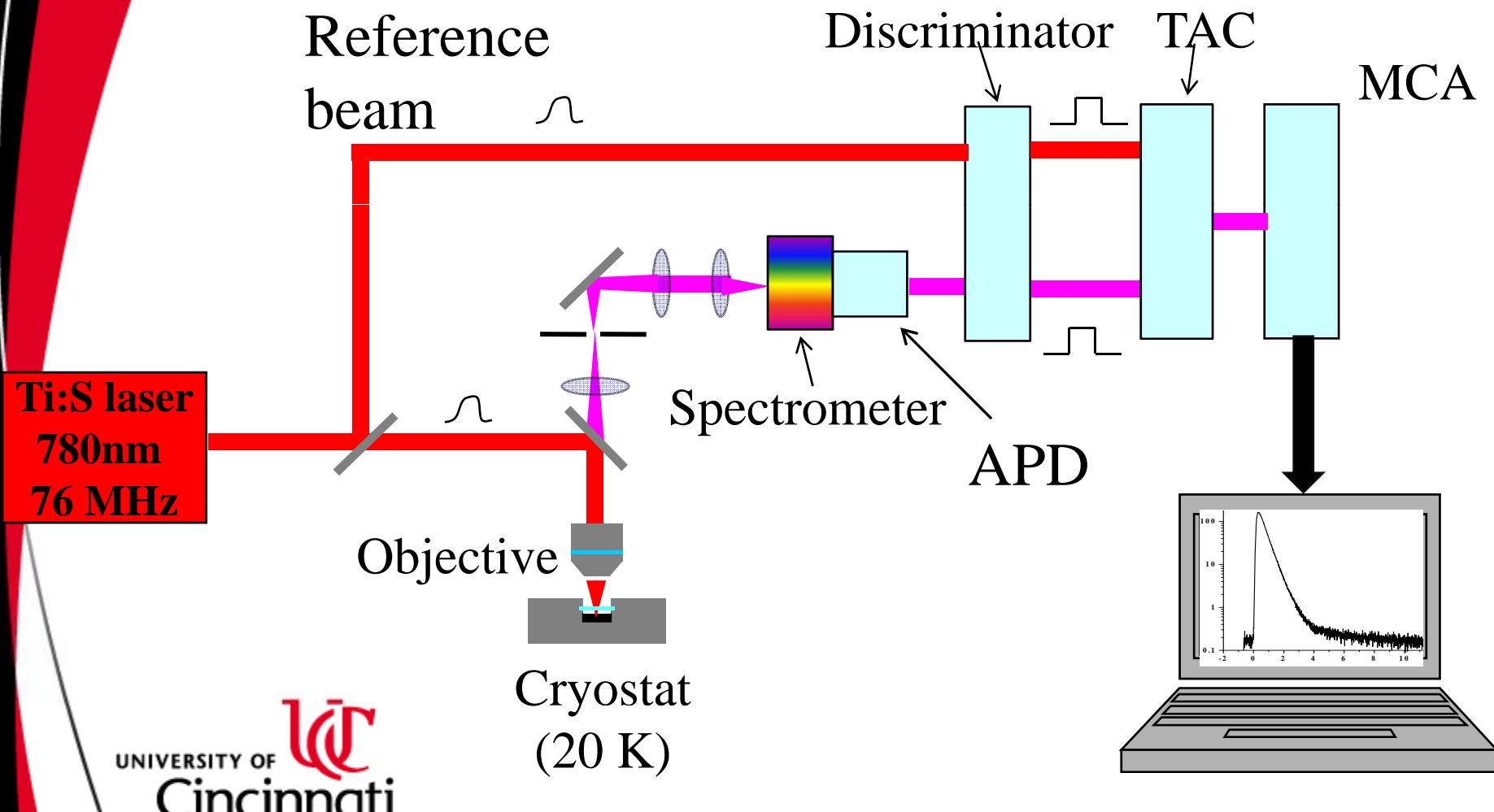


Sample Preparation

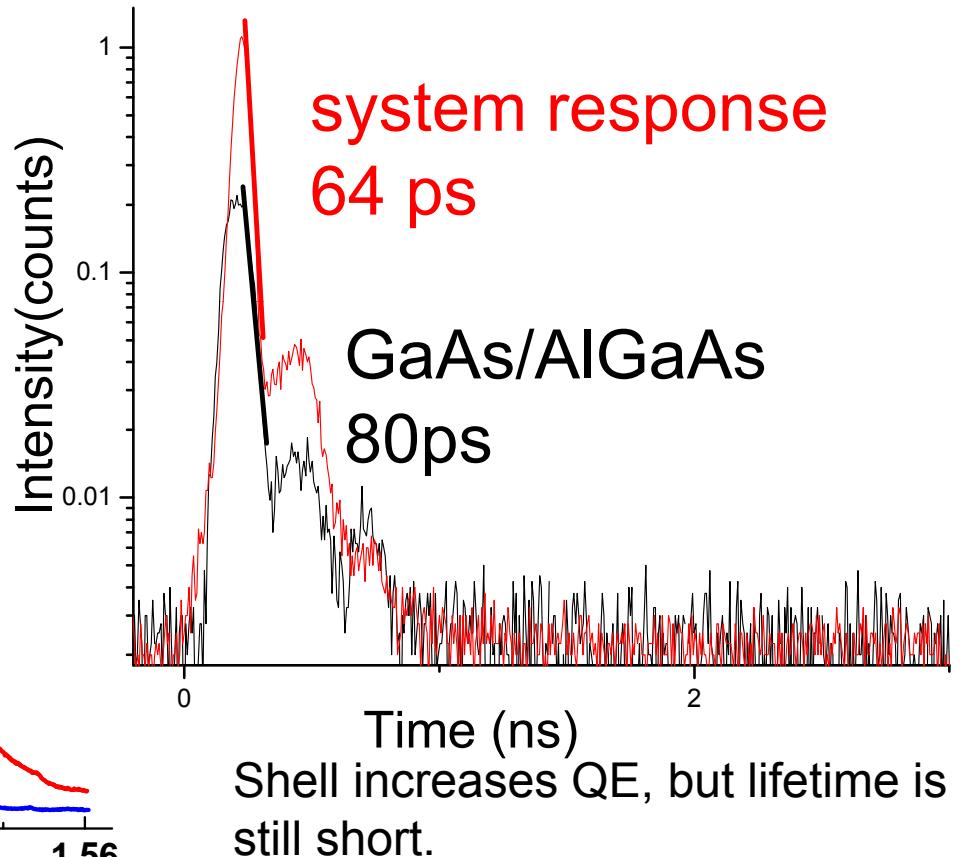
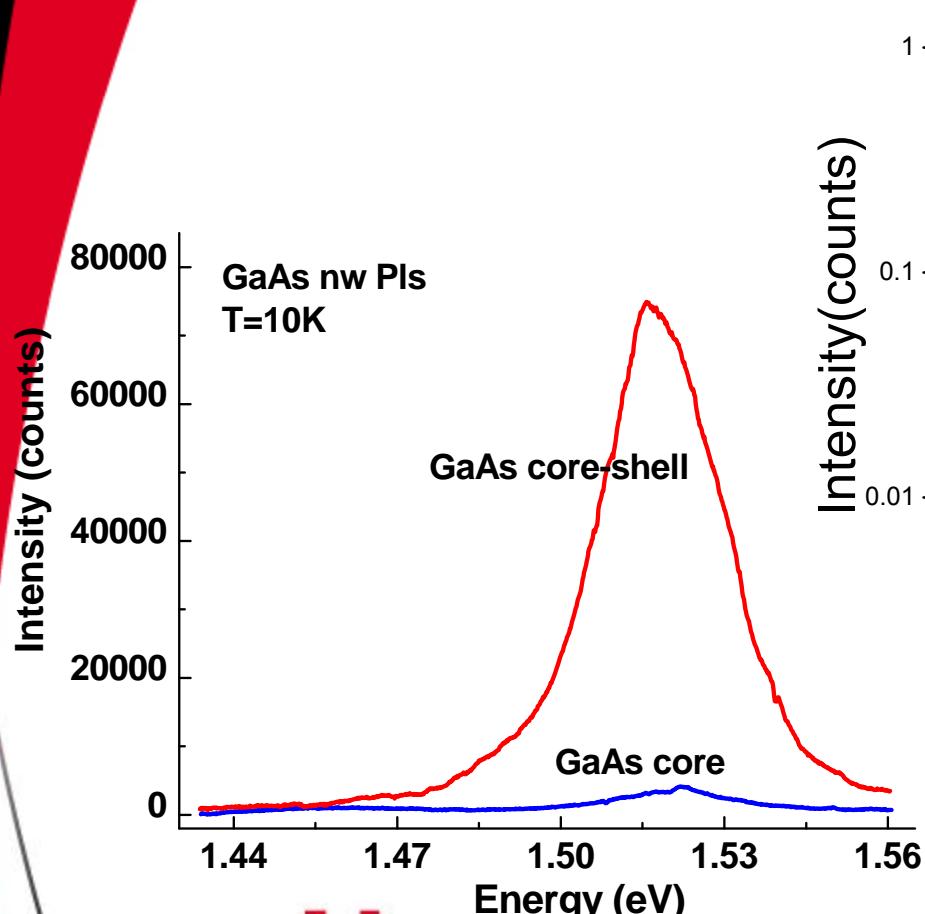
Mechanical transformation



Experimental Setup

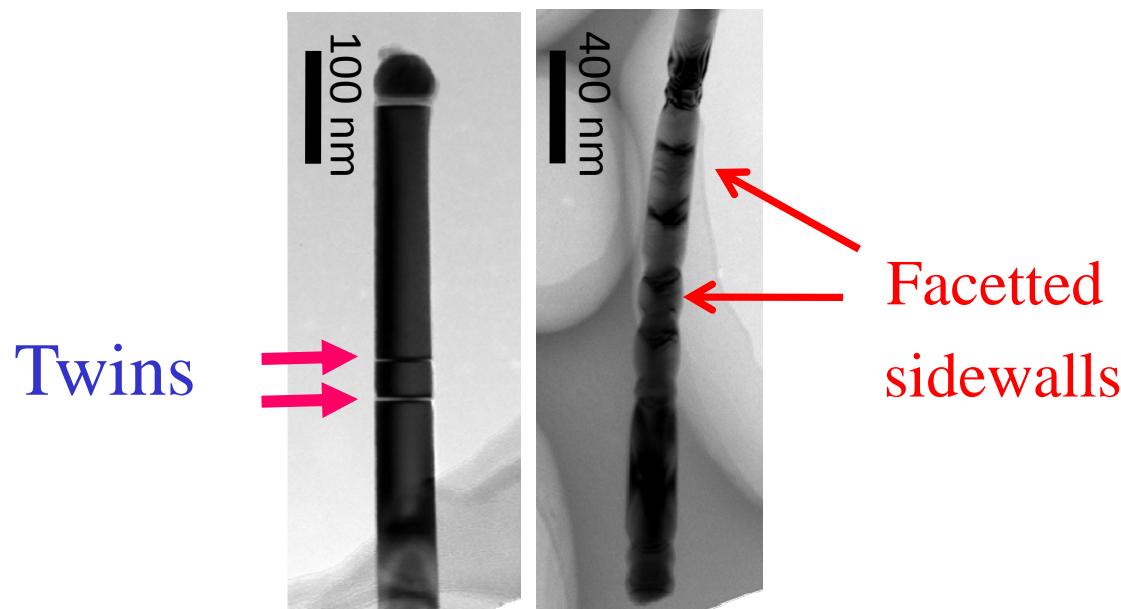


Short lifetimes, low Quantum Efficiency

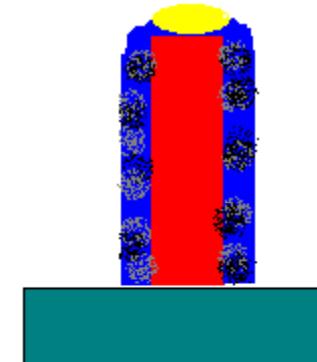


Possible Causes

- TEM of **GaAs core**



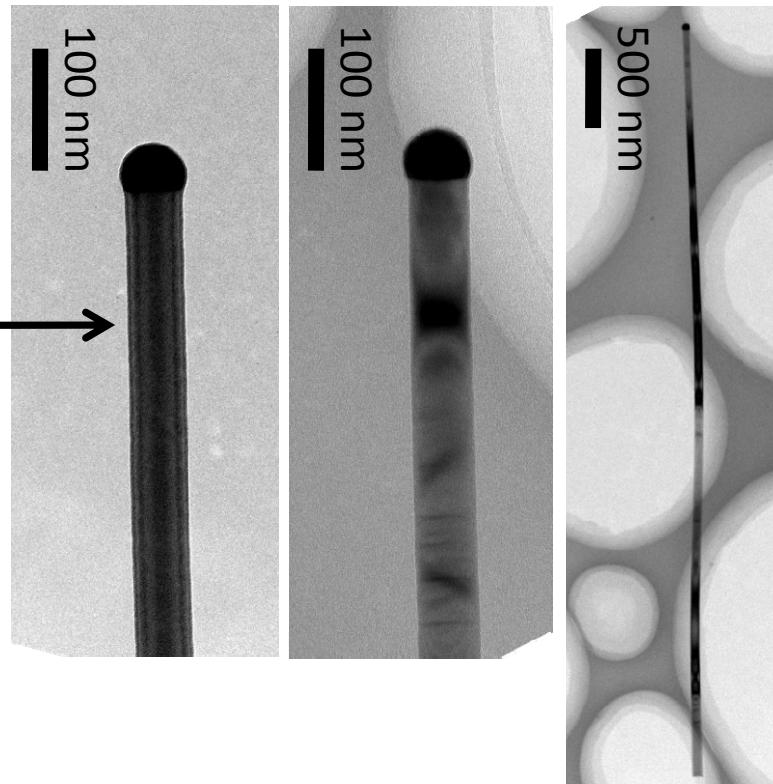
- Oxidation of **AlGaAs Shell**



A New Growth Procedure

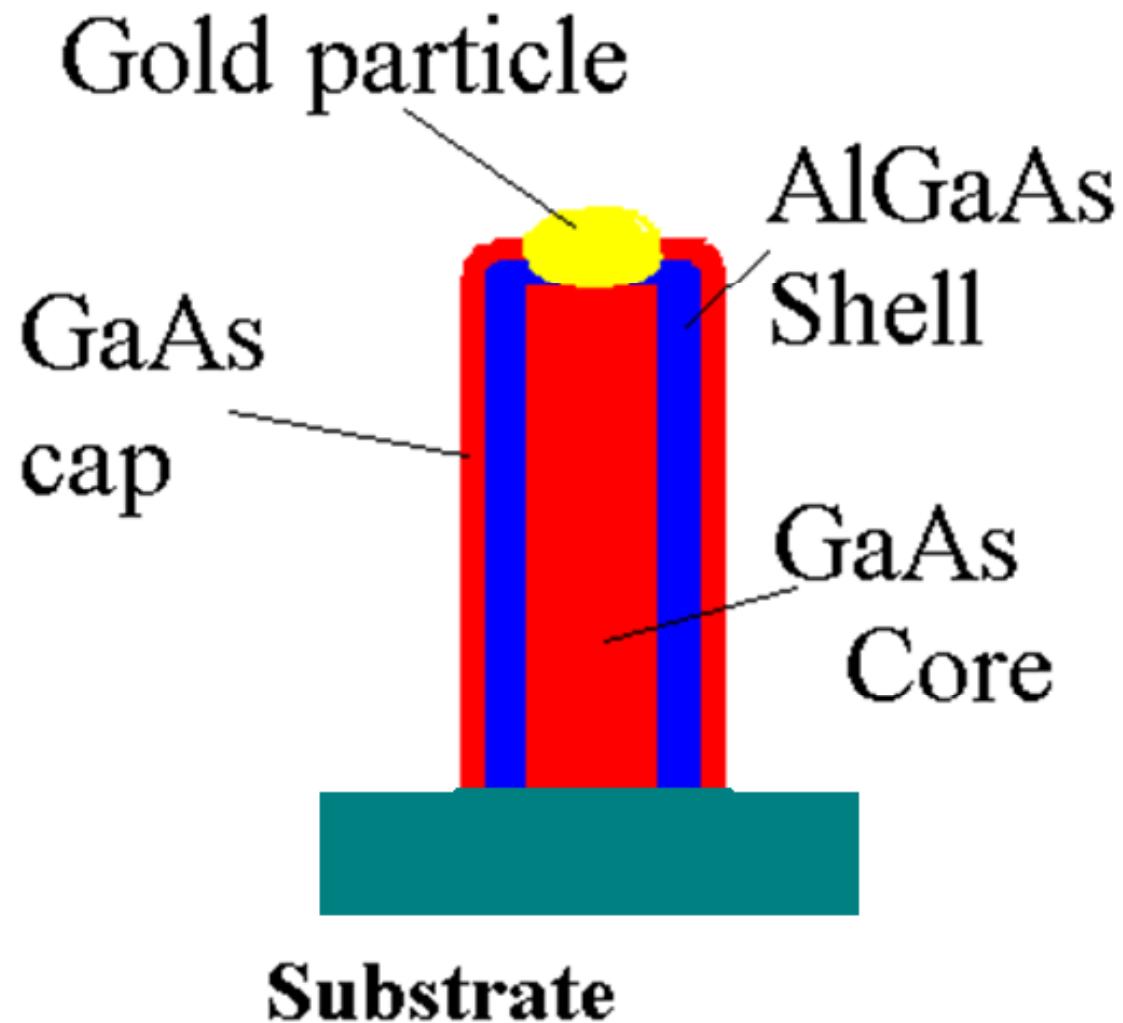
- Two-temperature growth

No twin defects !

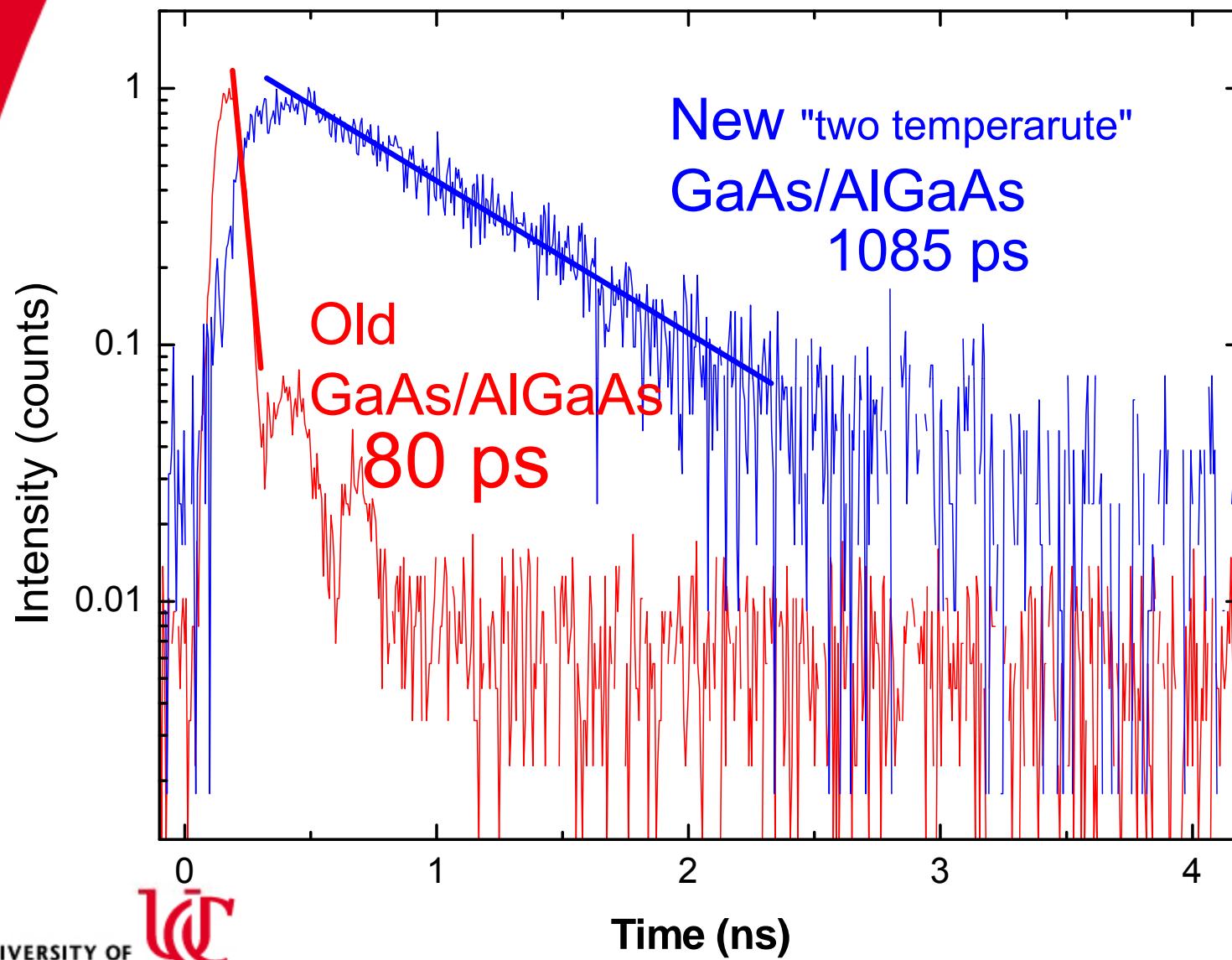


A second change

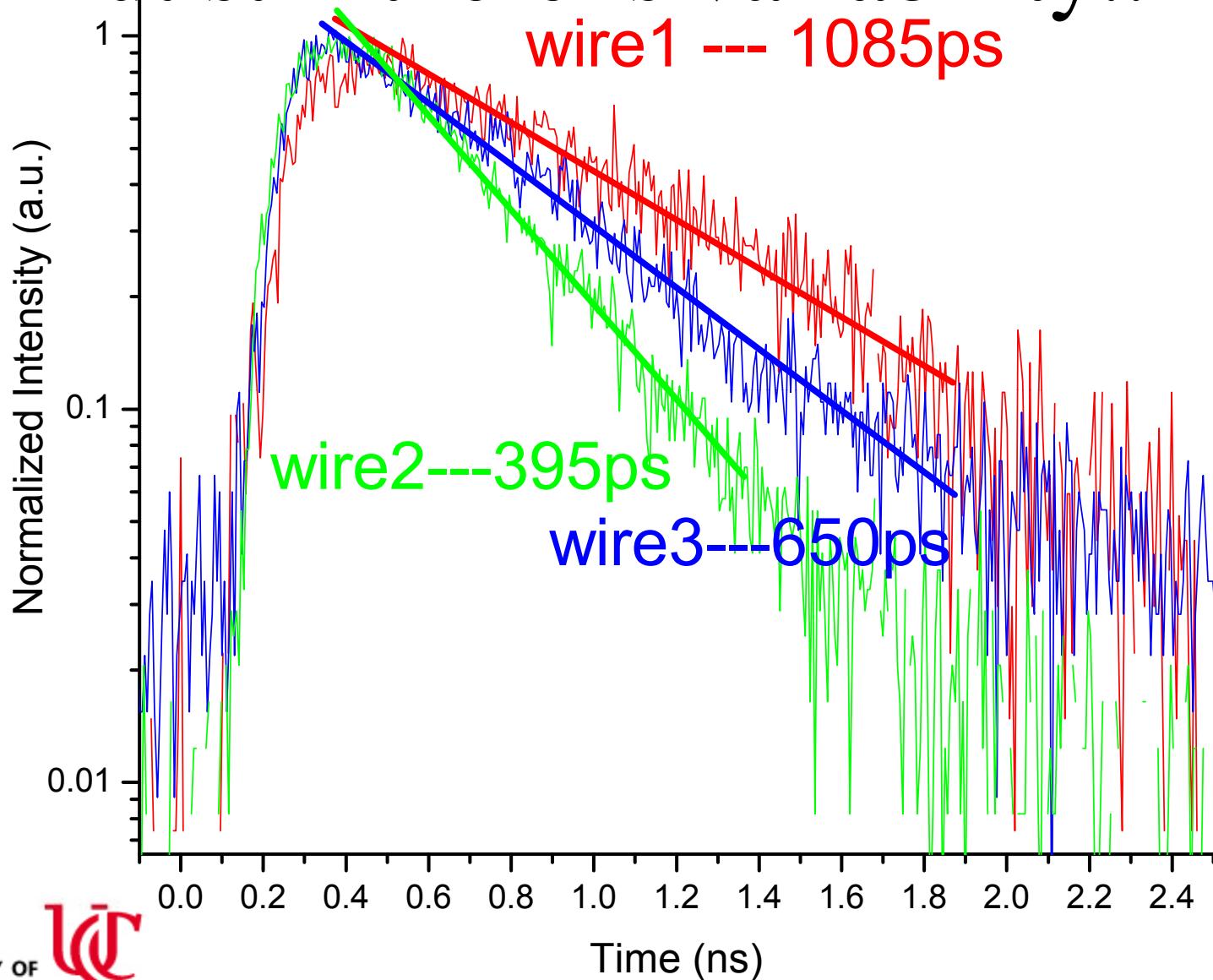
- Add 5nm GaAs cap ... eliminates oxidation.



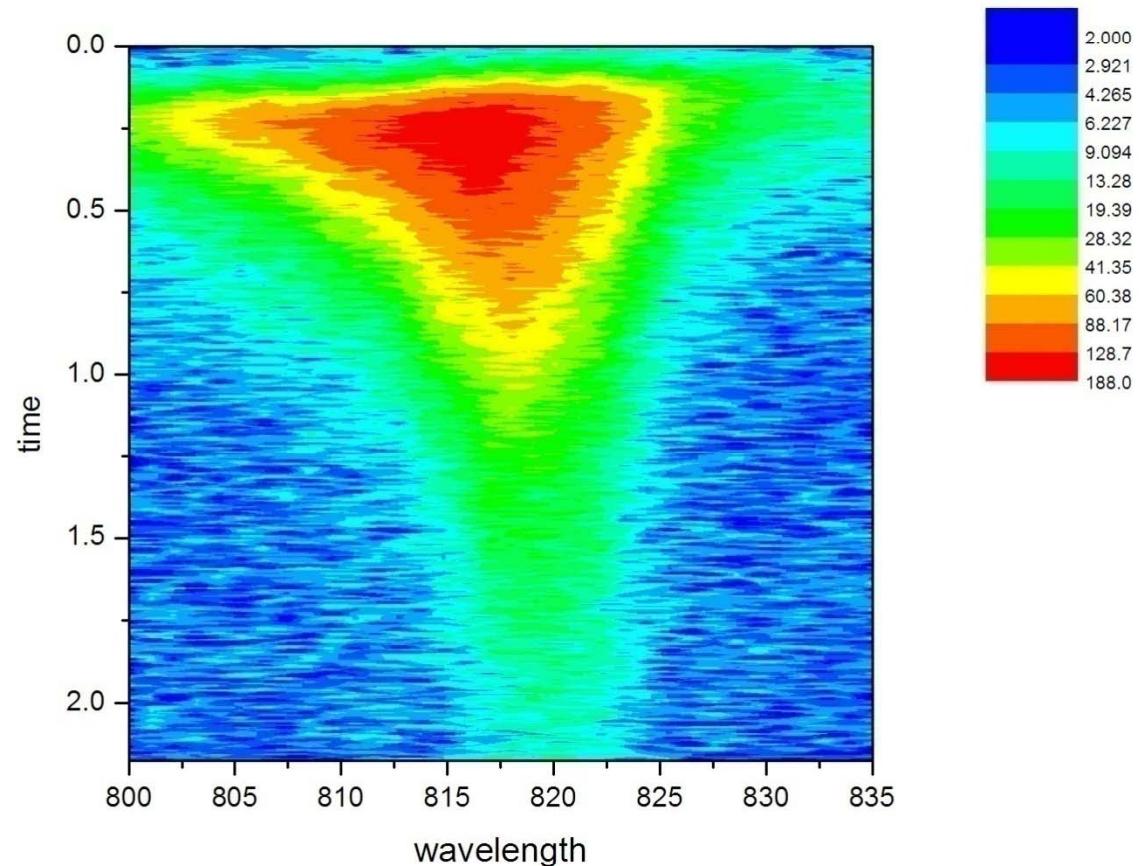
New growth Long lifetimes



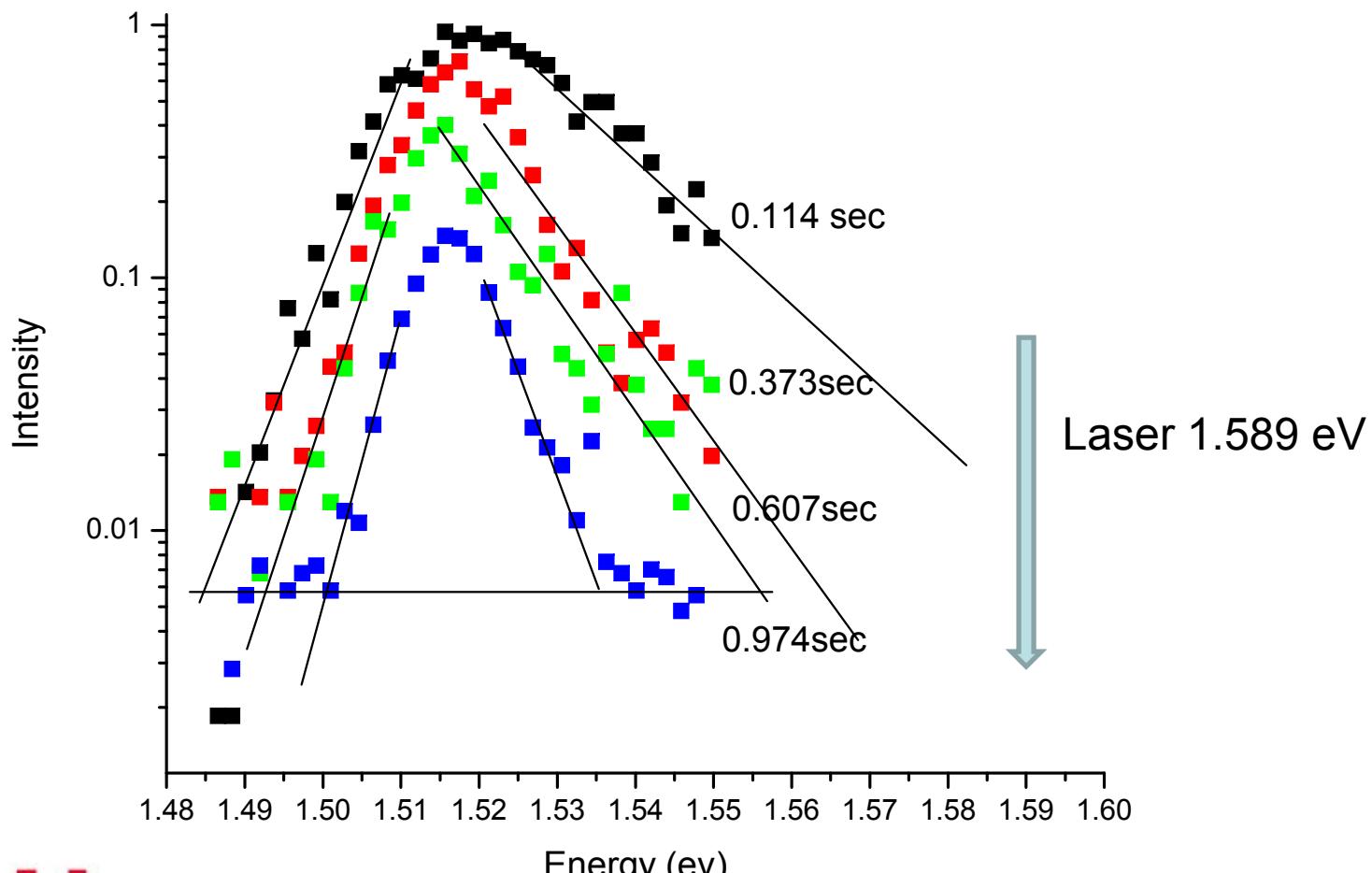
But still there is variability..



Time-resolved Spectral map of a single wire



Electron-hole plasma to exciton PL





Summary

- New growth method yields
 - Minimizes tapering
- Exhibits high quantum efficiency with a very long exciton lifetime ranging from 0.4 to 1.2 ns at 20 K.
- This will lead us to find electron Hole Plasma under high power pulsed excitation.